131,072 x 8 LOW VOLTAGE CMOS EPROM

NOVEMBER 1997

FEATURES

- Single 2.7V to 3.6V power supply
- · Fast access time: 90 ns
- JEDEC-approved pinout
- · Low power consumption
 - 20 μA (max) CMOS standby current
 - 10 mA (max) active current at 5 MHz
- High-speed programming
 - Typically less than 16 seconds
- Industrial and commercial temperature ranges available
- Standard 32-pin DIP, PLCC and TSOP packages

DESCRIPTION

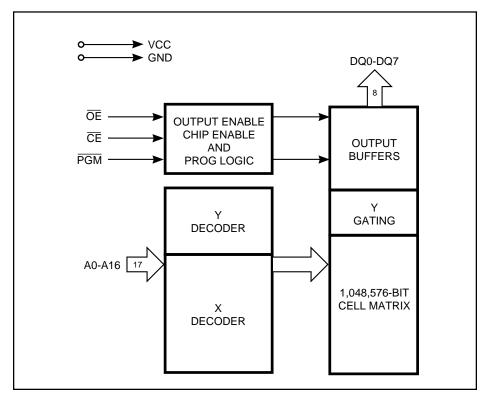
The *ISSI* IS27LV010 is a low voltage, low power, high-speed 1 megabit (128K-word by 8-bit) CMOS Programmable Read-Only Memory. It utilizes the standard JEDEC pinout making it funtionally compatible with the IS27C010 EPROM. The IS27LV010 operates from a 2.7V to 3.6V power supply.

The superior access time combined with low power consumption is the result of innovative design and process technology. Maximum power consumption in standby mode is $72\,\mu\text{W}$. If the device is constantly accessed at 5 MHz, then the maximum power consumption is increased to 36 mW. These power ratings are significantly lower than the standard IS27C010 EPROM.

The IS27LV010 uses ISSI's write programming algorithm which allows the entire chip to be programmed in typically less than 30 seconds.

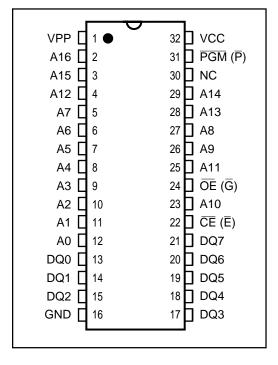
This product is available in One-Time Programmble (OTP) PDIP, PLCC, and TSOP packages over commercial and industrial temperature ranges.

FUNCTIONAL BLOCK DIAGRAM



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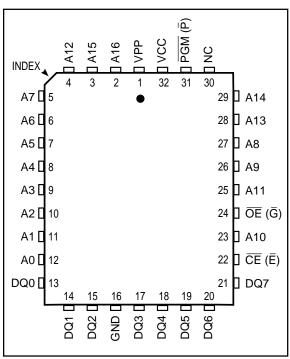
PIN CONFIGURATIONS 32-Pin DIP



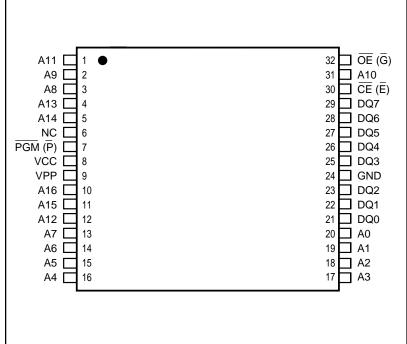
PIN DESCRIPTIONS

A0-A16	Address Inputs	
CE (E)	Chip Enable Input	
DQ0-DQ7	Data Inputs/Outputs	
ŌĒ (G)	Output Enable Input	
PGM (P)	Program Enable Input	
Vcc	Power Supply Voltage	
VPP	Program Supply Voltage	
GND	Ground	
NC	No Internal Connection	

32-Pin PLCC



32-Pin TSOP



FUNCTIONAL DESCRIPTION

Programming the IS27LV010

Upon delivery, the IS27LV010 has 1,048,576 bits in the "ONE", or HIGH state. "ZEROs" are loaded into the IS27LV010 through the procedure of programming.

The programming mode is entered when 12.5 ± 0.25 V is applied to the VPP pin, Vcc = 6V, \overline{CE} and \overline{PGM} is at V_{IL} , and OE is at VIH. For programming, the data to be programmed is applied eight bits in parallel to the data output pins.

The write programming algorithm reduces programming time by using 100 µs programming pulses followed by a byte verification to determine whether the byte has been successfully programmed. If the data does not verify, an additional pulse is applied for a maximum of 25 pulses. This process is repeated while sequencing through each address of the EPROM.

The write programming algorithm programs and verifies at Vcc = 6V and Vpp = 12.5V. After the final address is completed, all byte are compared to the original data with Vcc = 5.25V.

Program Inhibit

Programming of multiple IS27LV010s in parallel with different data is also easily accomplished. Except for CE, all like inputs of the parallel IS27LV010 may be common. A TTL low-level program pulse applied to an IS27LV010 CE input with $V_{PP} = 12.5 \pm 0.25 \text{V}$, PGM LOW and \overline{OE} HIGH will program that IS27LV010. A high-level CE input inhibits the other IS27LV010 from being programmed.

Program Verify

A verify should be performed on the programmed bits to determine that they were correctly programmed. The verify should be performed with \overline{OE} and \overline{CE} at VIL, \overline{PGM} at VIH, and VPP between 12.25V and 12.75V.

Auto Select Mode

The auto select mode allows the reading out of a binary code from an EPROM that will identify its manufacturer and type. This mode is intended for use by programming equipment for the purpose of automatically matching the device to be programmed with its corresponding programming algorithm. This mode is functional in the $25^{\circ}C \pm 5^{\circ}C$ ambient temperature range that is required when programming the IS27LV010.

To activate this mode, the programming equipment must force 12.0 \pm 0.5V on address line A9 of the IS27LV010.

Two identifier bytes may then be sequenced from the device outputs by toggling address line A0 from VIL to VIH. All other address lines must be held at VIL during auto select mode.

Byte 0 (A0 = VIL) represents the manufacturer code, and byte 1 (A0 = VIH), the device identifier code. For the IS27LV010, these two identifier bytes are given in the Mode Select table. All identifiers manufacturer and device codes will possess odd parity, with the MSB (DQ7) defined as the parity bit.

Read Mode

The IS27LV010 has two control functions, both of which must be logically satisfied in order to obtain data at the outputs. Chip Enable (\overline{CE}) is the power control and should be used for device selection. Assuming that addresses are stable, address access time (tACC) is equal to the delay from \overline{CE} to output (tce). Output Enable (\overline{OE}) is the output control and should be used to get data to the output pins, independent of device selection. Data is available at the outputs to after the falling edge of \overline{OE} assuming that \overline{CE} has been LOW and addresses have been stable for at least tacc - toe.

Standby Mode

The IS27LV010 has a standby mode which reduces the maximum Vcc active current. It is placed in standby mode when \overline{CE} is at $Vcc \pm 0.3V$. The amount of current drawn in standby mode depends on the frequency and the number of address pins switching. The IS27LV010 is specified with 50% of the address lines toggling at 5 MHz. A reduction of the frequency or quantity of address lines toggling will significantly reduce the actual standby current.

Output OR-Tieing

To accommodate multiple memory connections, a twoline control function is provided to allow for:

- 1. Low memory power dissipation, and
- Assurance that output bus contention will not occur.

It is recommended that \overline{CE} be decoded and used as the primary device-selecting function, while \overline{OE} be made a common connection to all devices in the array and connected to the READ line from the system control bus. This assures that all deselected memory devices are in their low-power standby mode and that the output pins are only active when data is desired from a particular memory device.

System Applications

During the switch between active and standby conditions, transient current peaks are produced on the rising and falling edges of Chip Enable. The magnitude of these transient current peaks is dependent on the output capacitance loading of the device at a minimum, a 0.1 μF ceramic capacitor (high-frequency, low inherent inductance) should be used on each device between Vcc and GND to minimize transient effects. In addition, to overcome the voltage drop caused by the inductive effects of the printed circuit board traces on EPROM arrays, a 4.7 μF bulk electrolytic capacitor should be used between Vcc and GND for each eight devices. The location of the capacitor should be close to where the power supply is connected to the array.

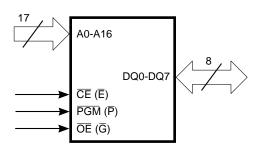
TRUTH TABLE(1,2)

Mode	CE	ŌĒ	PGM	A0	A9	VPP	Outputs
Read	VIL	VIL	Х	Х	Х	Vcc	D оит
Output Disable	VIL	ViH	Х	Х	Х	Vcc	Hi-Z
Standby	ViH	Х	Х	Х	Х	Vcc	Hi-Z
Program	VIL	ViH	VIL	Х	Х	Vpp	Din
Program Verify	VIL	VIL	ViH	Х	Х	Vpp	D оит
Program Inhibit	Vін	Х	Х	Х	Х	Vpp	Hi-Z
Auto Select ^(3,5) Manufacturer Code	VIL	VIL	Х	VIL	Vн	Vcc	D5H
Device Code	VIL	VIL	Χ	Vін	Vн	Vcc	0EH

Notes:

- 1. $VH = 12.0V \pm 0.5V$.
- 2. X = Either Vih or Vil.
- 3. A1-A8 = A10-A16 = VIL
- 4. See DC Programming Characteristics for VPP voltage during programming.
- 5. The IS27LV010 can use the same write algorithm during program as other IS27C010 or IS27010 devices.

LOGIC SYMBOL



ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Parameter	Value	Unit
VTERM	Terminal Voltage with Respect to GND		
	All pins except A9 and VPP	-0.6 to Vcc + $0.5^{(2)}$	V
	VPP	$Vcc - 0.3$ to $13.5^{(2,3)}$	V
	A9	-0.6 to 13.5 ^(2,3)	V
	Vcc	-0.6 to $7.0^{(2)}$	V
TA	Ambient Temperature with Power Applied	-65 to +125	°C
Tstg	Storage Temperature (OTP)	-65 to +125	°C
Tstg	Storage Temperature (All others)	-65 to +150	°C

Notes:

- Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the
 device. This is a stress rating only and functional operation of the device at these or any other conditions above
 those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum
 rating conditions for extended periods may affect reliability.
- 2. Minimum DC input voltage is -0.5V. During transitions, inputs may undershoot to -2.0V for periods less than 10 ns. Maximum DC voltage on output pins is Vcc + 0.5V which may overshoot to Vcc + 2.0V for periods less than 10 ns.
- 3. Maximum DC voltage on A9 or VPP may overshoot to +13.5V for periods less than 10 ns.

OPERATING RANGE

Range	Ambient Temperature	Vcc
Commercial	0°C to +70°C	2.7 – 3.6V
Industrial ⁽¹⁾	−40°C to +85°C	2.7 – 3.6V

Note:

1. Operating ranges define those limits between which the functionally of the device is guaranteed.

DC ELECTRICAL CHARACTERISTICS(1,2,3) (Over Operating Range)

Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Vон	Output HIGH Voltage	$Vcc = Min., IoH = -400 \mu A$	2.4	_	V
Vol	Output LOW Voltage	Vcc = Min., IoL = 2.0 mA	_	0.4	V
ViH	Input HIGH Voltage(4)		2.0	Vcc + 0.5	V
VIL	Input LOW Voltage(4)		-0.3	0.8	V
ILI	Input Load Current	Vin = 0V to +Vcc	_	5	μΑ
ILO	Output Leakage Current	Vout = 0V to +Vcc	_	5	μΑ

- 1. Vcc must be applied simultaneously or before VPP and removed simultaneously or after VPP. Never try to force VPP LOW to 1V below Vcc. Manufacturer suggests to tie VPP and Vcc together during the READ operation.
- 2. Caution: the IS27LV010 must not be removed from (or inserted into) a socket when Vcc or VPP is applied.
- 3. Minimum DC input voltage is -0.5V. During transitions, the inputs may undershoot to -2.0V for periods less than 10 ns. Maximum DC voltage on output pins is Vcc + 0.5V which may overshoot to Vcc + 2.0V for periods less than 10 ns.
- 4. Tested under static DC conditions.

POWER SUPPLY CHARACTERISTICS(1,2,5) (Over Operating Range)

Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Icc1	Vcc Operating Supply Current ⁽³⁾	Vcc = Max., \overline{CE} = V _{IL} lout = 0 mA, f = 5 MHz (Open outputs)	_	10	mA
IPP1	VPP Current During Read ⁽⁴⁾	$V_{CC} = Max., \overline{CE} = \overline{OE} = V_{IL}$ $V_{PP} = V_{CC}$	_	10	μΑ
Iccsb0	Vcc CMOS Standby Current	CE = Vcc + 0.3V (No toggling)	_	20	μΑ
Iccs _B 1	Vcc TTL Standby Current	CE = Vін (No toggling)	_	200	μΑ

Notes:

- 1. Vcc must be applied simultaneously or before VPP and removed simultaneously or after VPP. Never try to force VPP LOW to 1V below Vcc. Manufacturer suggests to tie VPP and Vcc together during the READ operation.
- 2. Caution: the IS27LV010 must not be removed from (or inserted into) a socket when Vcc or VPP is applied.
- 3. Icc1 is tested with $\overline{OE} = V_{IH}$ to simulate open outputs.
- 4. Maximum active power usage is the sum of Icc and IPP.
- 5. Minimum DC input voltage is -0.5V. During transitions, the inputs may undershoot to -2.0V for periods less than 10 ns. Maximum DC voltage on output pins is Vcc + 0.5V which may overshoot to Vcc + 2.0V for periods less than 10 ns.

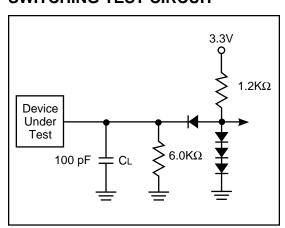
CAPACITANCE(1,2,3)

Symbol	Parameter	Conditions	Тур.	Max.	Unit
Cin	Input Capacitance	Vin = 0V	8	10	pF
Соит	Output Capacitance	Vout = 0V	8	12	pF

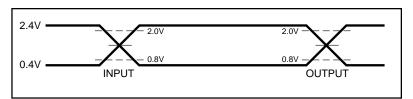
Notes:

- 1. Typical values are for nominal supply voltage.
- 2. This parameter is only sampled, but not 100% tested.
- 3. Test conditions: TA = 25°C, f = 1 MHz.

SWITCHING TEST CIRCUIT



SWITCHING TEST WAVEFORM



Notes:

AC Testina:

- 1. Inputs are driven at 2.4V for a logic "1" and 0.4V for a logic "0".
- 2. Input pulse rise and fall times are \leq 20 ns.

SWITCHING CHARACTERISTICS(1,3,4) (Over Operating Range)

JEDEC	Std.			-(90	-1	12	-1	15	
Symbol	Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Min.	Max.	Unit
t avqa	tacc	Address to Output Delay	$\overline{CE} = \overline{OE} = V_{IL}$	_	90	_	120	_	150	ns
t ELQV	tce	Chip Enable to Output Delay	OE = VIL CL = CL1	_	90	_	120	_	150	ns
tGLQV	toe	Output Enable to Output Delay	CE = VIL	_	45	_	50	_	65	ns
teнoz, tgнqz	t DF ⁽²⁾	Chip Enable HIGH or Output Enable HIGH, whichever comes first, to Output Float		_	30	_	35	_	35	ns
tavox	tон	Output Hold from Address, CE or OE whichever occured first		0	_	0	_	0	_	ns

Notes:

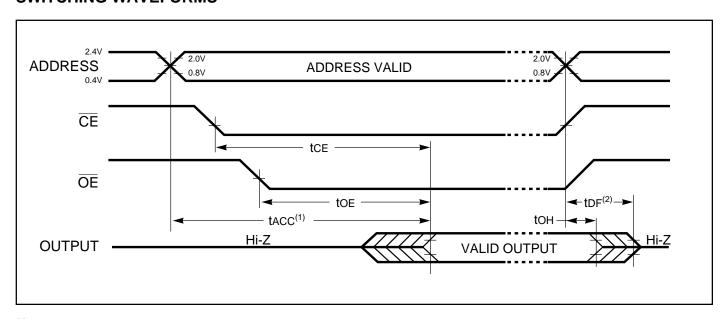
- 1. Vcc must be applied simultaneously or before VPP and removed simultaneously or after VPP.
- 2. This parameter is only sampled, not 100% tested.
- 3. Caution: The IS27LV010 must not be removed from (or inserted into) a socket or board when VPP or Vcc applied.
- 4. Output Load: 1 TTL gate and C_L =100 pF.

Input Rise and Fall times: 20 ns.

Input Pulse Levels: 0.4V to 2.4V.

Timing Measurement Reference Level: 0.8V to 2V for inputs and outputs.

SWITCHING WAVEFORMS



- 1. \overline{OE} may be delayed \underline{up} to \underline{tacc} toe after the falling edge of \overline{CE} without impact on tacc. 2. \underline{tof} is specified from \overline{OE} or \overline{CE} , whichever occurs first.

DC PROGRAMMING CHARACTERISTICS(1,2,3,4) (TA = +25°C ± 5 °C)

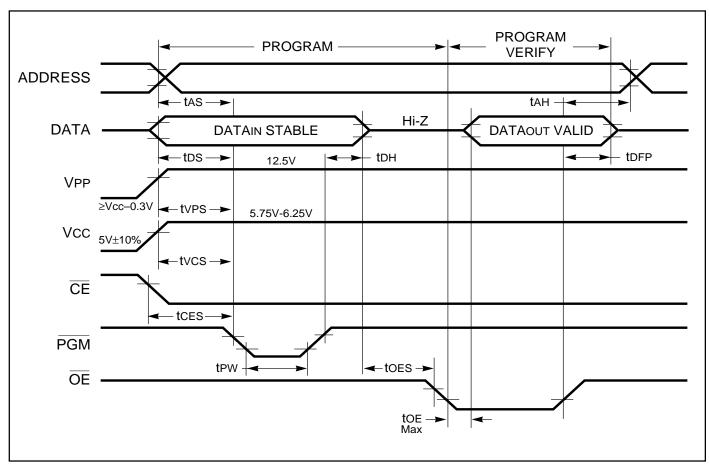
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Vон	Output HIGH Voltage During Verify	Іон = –400 μА	2.4	_	V
Vol	Output LOW Voltage During Verify	IoL = 2.1 mA	_	0.45	V
ViH	Input HIGH Voltage		2.0	Vcc + 0.5	V
VIL	Input LOW Voltage (All Inputs)		-0.3	0.8	V
Vн	A9 Auto Select Voltage		11.5	12.5	V
lu	Input Current (All Inputs)	VIN = VIL or VIH	_	10.0	μΑ
Icc	Vcc Supply Current (Program & Verify)		_	50	mA
I PP	VPP Supply Current	CE = VIL, OE = VIH	_	30	mA
Vcc	Supply Voltage		5.75	6.25	V
VPP	Programming Voltage		12.25	12.75	V

SWITCH PROGRAMMING CHARACTERISTICS(1,2,3,4) (TA = +25°C \pm 5°C)

JEDEC	Std.	Danamatan	B#*	N 4	119
Symbol	Symbol	Parameter	Min.	Max.	Unit
t avel	t AS	Address Setup Time	2	_	μs
t DZGL	toes	OE Setup Time	2	_	μs
t DVEL	tos	Data Setup Time	2	_	μs
t GHAX	t ah	Address Hold Time	0	_	μs
t EHDX	t DH	Data Hold Time	2	_	μs
t GHQZ	t DFP	OE HIGH to Output Float Delay	0	130	ns
tvps	t vps	VPP Setup Time	2	_	μs
teleh1	t PW	PGM Program Pulse Width	95	105	μs
tvcs	tvcs	Vcc Setup Time	2		μs
t ELPL	tces	CE Setup Time	2	_	μs
t GLQV	t oe	Data Valid from OE	_	150	ns

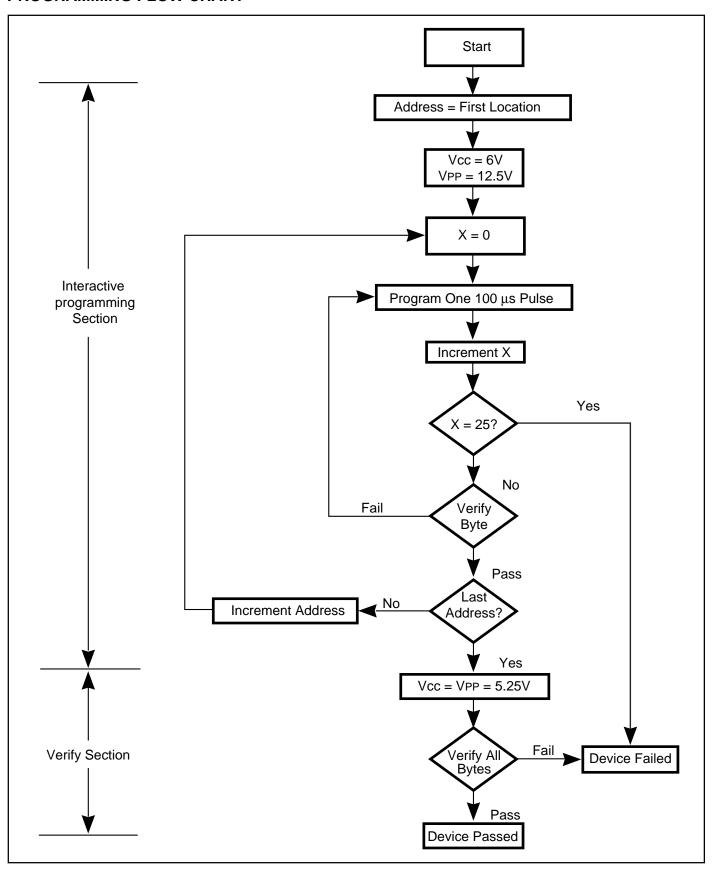
- 1. Vcc must be applied simultaneously or before VPP and removed simultaneously or after VPP.
- 2. VPP must be \geq Vcc during the entire programming and verifying procedure.
- 3. When programming IS27LV010, a 0.1 μF capacitor is required across VPP and ground to suppress spurious voltage transients which may damage the device.
- 4. Programming characteristics are sampled but not 100% tested at worst-case conditions.

PROGRAMMING ALGORITHM WAVEFORM(1,2)



- The timing reference level is 0.8V for V_{IL} and 2.0V for V_{IH}.
- 2. toe and tofp are characteristics of the device but must be accommodated by the programmer.

PROGRAMMING FLOW CHART



ORDERING INFORMATION

Commercial Rangle: 0°C to +70°C

Speed (ns)	Order Part Number	Package
90	IS27LV010-90W IS27LV010-90PL IS27LV010-90T	600-mil Plastic DIP PLCC – Plastic Leaded Chip Carrier TSOP
120	IS27LV010-12W IS27LV010-12PL IS27LV010-12T	600-mil Plastic DIP PLCC – Plastic Leaded Chip Carrier TSOP
150	IS27LV010-15W IS27LV010-15PL IS27LV010-15T	600-mil Plastic DIP PLCC – Plastic Leaded Chip Carrier TSOP

ORDERING INFORMATION

Industrial Rangle: -40°C to +85°C

Speed (ns)	Order Part Number	Package
90	IS27LV010-90PLI IS27LV010-90TI	PLCC – Plastic Leaded Chip Carrier TSOP
120	IS27LV010-12PLI IS27LV010-12TI	PLCC – Plastic Leaded Chip Carrier TSOP
150	IS27LV010-15PLI IS27LV010-15TI	PLCC – Plastic Leaded Chip Carrier TSOP



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